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(54) Title: METHODS FOR DETERMINING SUITABILITY OF SILICON SUBSTRATES FOR EPITAXY



FIG. 1

(57) Abstract: Methods for determining suitability of a silicon substrate for epitaxy and/or for determining slip resistance during epitaxy and post-epitaxy thermal treatment are disclosed. The methods involve evaluating different substrates of the epitaxial wafers by imaging the wafer by infrared depolarization. An infrared depolarization parameter is generated for each epitaxial wafer. The parameters may be compared to determine which substrates are well-suited for epitaxial and/or post-epi heat treatments.



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